

Vishay Semiconductors

PARAMETER	SYMBOL		VALUES	UNITS		
Maximum average on-state current	I _{T(AV)}		TEST CONDITIONS	8		
Maximum RMS on-state current	I _{T(RMS)}	T _C = 108 °C, 1	$T_C = 108 \text{ °C}, 180^\circ \text{ conduction, half sine wave}$			
Maximum peak one-cycle		10 ms sine pu	lse, rated V_{RRM} applied, T_{J} = 125 °C	95	A	
non-repetitive surge current	I _{TSM}	10 ms sine pu	lse, no voltage reapplied, $T_J = 125 \ ^{\circ}C$	110		
Maximum I ² t for fusing	l ² t	10 ms sine pu	lse, rated V_{RRM} applied, T_J = 125 °C	45	A ² s	
	141	10 ms sine pu	64	A-5		
Maximum I ² \sqrt{t} for fusing	l²√t	t = 0.1 ms to 1	640	A²√s		
Maximum on-state voltage drop	V _{TM}	8 A, T _J = 25 °C	1.2	V		
On-state slope resistance	r _t	T.I = 125 °C		16.2	mΩ	
Threshold voltage	V _{T(TO)}	1J = 125 C		0.87	V	
Maximum reverse and direct leakage current	1/1	T _J = 25 °C	V _B = Rated V _{BBM} /V _{DBM}	0.05		
Maximum reverse and direct leakage current	I _{RM} /I _{DM}	T _J = 125 °C	VR - nated VRRM/ VDRM	1.0		
Typical holding current	Ι _Η	Anode supply T _J = 25 °C	30	mA		
Maximum latching current	١L	Anode supply	50			
Maximum rate of rise of off-state voltage	dV/dt	T _J = T _J max., I	150	V/µs		
Maximum rate of rise of turned-on current	dl/dt			100	A/µs	

TRIGGERING									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Maximum peak gate power	P _{GM}		8.0	W					
Maximum average gate power	P _{G(AV)}		2.0	vv					
Maximum peak positive gate current	+ I _{GM}		1.5	А					
Maximum peak negative gate voltage	- V _{GM}		10	V					
		Anode supply = 6 V, resistive load, T_J = - 65 °C	20						
Maximum required DC gate current to trigger	I _{GT}	Anode supply = 6 V, resistive load, T_J = 25 °C	15	mA					
		Anode supply = 6 V, resistive load, T_J = 125 °C	10						
		Anode supply = 6 V, resistive load, T_J = - 65 °C	1.2	V					
Maximum required DC gate voltage to trigger	V _{GT}	Anode supply = 6 V, resistive load, $T_J = 25 \ ^{\circ}C$	1						
		Anode supply = 6 V, resistive load, $T_J = 125 \text{ °C}$	0.7	v					
Maximum DC gate voltage not to trigger	V _{GD}	T 105 °C V Dated value	0.2						
Maximum DC gate current not to trigger	I _{GD}	T _J = 125 °C, V _{DRM} = Rated value	0.1	mA					

SWITCHING									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Typical turn-on time	t _{gt}	T _J = 25 °C	0.8						
Typical reverse recovery time	t _{rr}	T.I = 125 °C	3	μs					
Typical turn-off time	tq	ij= 125 C	100						

Revision: 08-Jul-15

2

Document Number: 94499

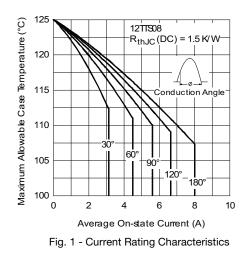
For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>

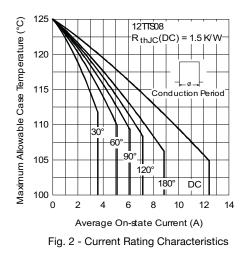
VS-12TTS08SPbF Series

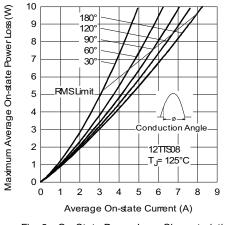


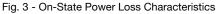
Vishay Semiconductors

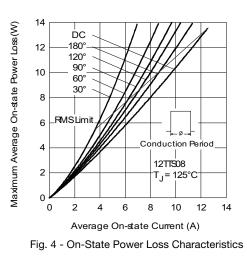
THERMAL AND MECHANICAL SPECIFICATIONS									
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Maximum junction and storage temperature range		T _J , T _{Stg}		-40 to +125	°C				
Maximum thermal resistance, junction to case		R _{thJC}	DC operation	1.5					
Maximum thermal resistance, junction to ambient		R _{thJA}		62	°C/W				
Typical thermal resistance, case to heatsink		R _{thCS}	Mounting surface, smooth and greased	0.5					
Approvimate weight				2	g				
Approximate weight				0.07	oz.				
Mounting torgue	minimum			6 (5)	kgf ⋅ cm				
Mounting torque —	maximum			12 (10)	(lbf · in)				
Marking device			Case style D ² PAK (SMD-220)	12TT:	S08S				











Revision: 08-Jul-15

3

Document Number: 94499

For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>

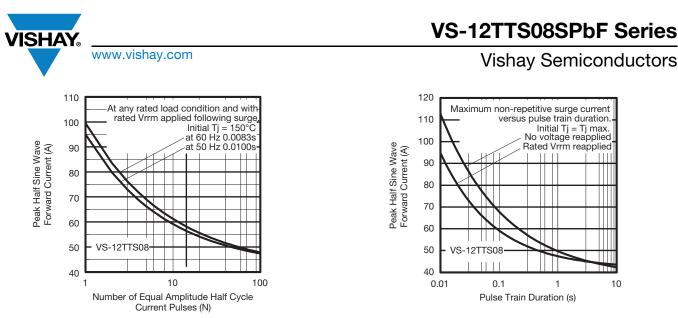
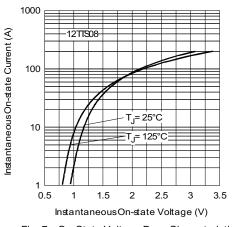


Fig. 5 - Maximum Non-Repetitive Surge Current

Fig. 6 - Maximum Non-Repetitive Surge Current





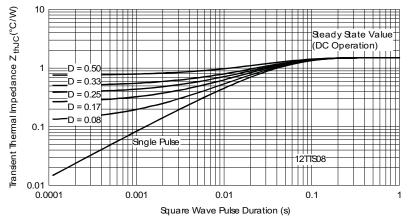


Fig. 8 - Thermal Impedance ZthJC Characteristics

VS-12TTS08SPbF Series

Vishay Semiconductors

ORDERING INFORMATION TABLE

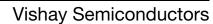
Device code	VS-	12	т	т	S	08	S	TRL	PbF
	1	2	3	4	5	6	7	8	9
	1 - 2 - 3 -	Cur	rent rati	niconduo ng (12.5 iguratior	A)	oduct			
	4 -	T = Pac	single tl kage: TO-220	nyristor					
	5 -	Тур	e of silio		ery recti	ifier			
	6 - 7 -		-	ng (08 = D ² PAK	-		rsion		
	8 -	• TF	-	be e and re be and re	-		-		
	9 -		-	(Pb)-fre		c onorite			

ORDERING INFORMATION (Example)									
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION						
VS-12TTS08SPbF	50	1000	Antistatic plastic tubes						
VS-12TTS08STRRPbF	800	800	13" diameter reel						
VS-12TTS08STRLPbF	800	800	13" diameter reel						

LINKS TO RELATED DOCUMENTS						
Dimensions	www.vishay.com/doc?95046					
Part marking information	www.vishay.com/doc?95054					
Packaging information	www.vishay.com/doc?95032					

VISHAY	
	www.vishay.com

Outline Dimensions

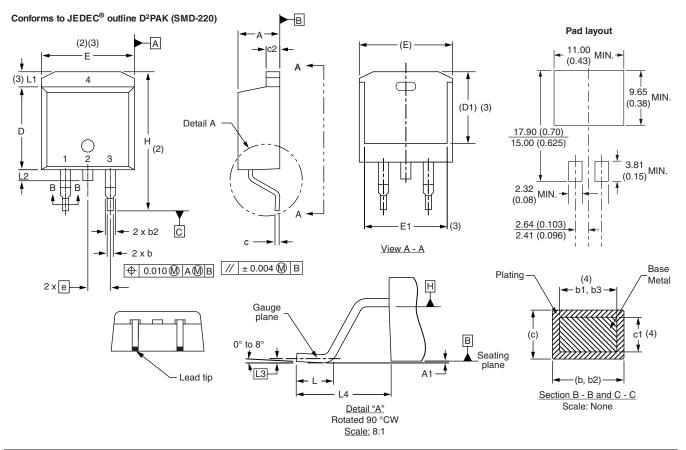


D²PAK

DIMENSIONS in millimeters and inches

www.vishay.com

ISHA



SYMBOL	MILLIM	IETERS	INC	HES	NOTES	NOTES	SYMBOL	MILLIMETERS		INCHES		NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES		STWDUL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			E	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100) BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3	0.25	BSC	0.010) BSC	
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5 M-1994

⁽²⁾ Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

⁽³⁾ Thermal pad contour optional within dimension E, L1, D1 and E1

(4) Dimension b1 and c1 apply to base metal only

⁽⁵⁾ Datum A and B to be determined at datum plane H

⁽⁶⁾ Controlling dimension: inch

⁽⁷⁾ Outline conforms to JEDEC[®] outline TO-263AB

Revision: 08-Jul-15

1

For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>



Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.